



1M x 4 DRAM DYNAMIC RANDOM-ACCESS MEMORY

AVAILABLE AS MILITARY SPECIFICATIONS

- SMD 5962-90847
- MIL-STD-883

FEATURES

- Organized 1,048,576 x 4
- Single +5V ±10% power supply
- Enhanced Page-Mode operation for faster memory access
 - ✓ Higher data bandwidth than conventional page-mode parts
 - ✓ Random Single-Bit Access within a row with a column address
- CAS\ -Before-RAS\ (CBR) Refresh
- Long Refresh period: 1024-cycle Refresh in 16ms (Max)
- 3-State unlatched Output
- Low Power Dissipation
- All Inputs/Outputs and Clocks are TTL Compatible
- Processing to MIL-STD-883, Class B available

OPTIONS

• Timing

80ns access	-8
100ns access	-10
120ns access	-12

• Package(s)

Ceramic DIP (400mils)	JD	No. 113
-----------------------	----	---------

• Operating Temperature Ranges

Industrial (-40°C to +85°C)	IT
Military (-55°C to +125°C)	XT

GENERAL DESCRIPTION

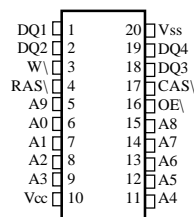
The SMJ44400 is a series of 4,194,304-bit dynamic random-access memories (DRAMs), organized as 1,048,576 words of four bits each. This series employs state-of-the-art technology for high performance, reliability, and low-power operation.

The SMJ44400 features maximum row access times of 80ns, 100ns, and 120ns. Maximum power dissipation is as low as 360mW operating and 22mW standby.

All inputs and outputs, including clocks, are compatible with Series 54 TTL. All addresses and data-in lines are latched on-chip to simplify system design. Data out is unlatched to allow greater system flexibility.

PIN ASSIGNMENT (Top View)

20-Pin DIP (JD)
(400 MIL)



Pin Name	Function
A0 - A9	Address Inputs
CAS\	Column-Address Strobe
DQ1 - DQ4	Data Inputs/Outputs
OE\	Output Enable
RAS\	Row-Address Strobe
W\	Write Enable
Vcc	5V Supply
Vss	Ground

The SMJ44400 is offered in a 400-mil, 20-pin ceramic side-braced dual-in-line package (JD suffix) that is characterized for operation from -55°C to +125°C.

OPERATION

Enhanced Page Mode

Enhanced page-mode operation allows faster memory access by keeping the same row address while selecting random column addresses. The time for row-address setup and hold and address multiplex is eliminated. The maximum number of columns that can be accessed is determined by the maximum RAS\ low time and the CAS\ page cycle time used. With minimum CAS\ page cycle time, all 1024 columns specified by column addresses A0 through A9 can be accessed without intervening RAS\ cycles.

Unlike conventional page-mode DRAMs, the column-address buffers in this device are activated on the

(continued)

**For more products and information
please visit our web site at
www.austinsemiconductor.com**



Enhanced Page Mode (continued)

falling edge of RAS \setminus . The buffers act as transparent or flow-through latches while CAS \setminus is high. The falling edge of CAS \setminus latches the column addresses. This feature allows the SMJ44400 to operate at a higher data bandwidth than conventional page-mode parts, since data retrieval begins as soon as column address is valid rather than when CAS \setminus goes low. This performance improvement is referred to as enhanced page mode. Valid column address can be presented immediately after row address hold time has been satisfied, usually well in advance of the maximum (access time from column address) has been satisfied. In the event that column addresses for the next cycle are valid at the time CAS \setminus goes high, access time for the next cycle is determined by the later occurrence of t_{CAC} or t_{CPA} (access time from rising edge of CAS \setminus).

Address (A0-A9)

Twenty address bits are required to decode 1 of 1,048,576 storage cell locations. Ten row-address bits are set up on inputs A0 through A9 and latched onto the chip by RAS \setminus . The ten column-address bits are set up on pins A0 through A9 and latched onto the chip by CAS \setminus . All addresses must be stable on or before the falling edges of RAS \setminus and CAS \setminus . RAS \setminus is similar to a chip enable in that it activates the sense amplifiers as well as the row decoder. CAS \setminus is used as a chip select, activating the output buffer as well as latching the address bits into the column-address buffer.

Write Enable (W)

The read or write mode is selected through W \setminus . A logic high on the W \setminus input selects the read mode and a logic low selects the write mode. The write-enable terminal can be driven from standard TTL circuits without a pullup resistor. The data input is disabled when the read mode is selected. When W \setminus goes low prior to CAS \setminus (early write), data out remains in the high-impedance state for the entire cycle permitting a write operation independent of the state of OE \setminus . This permits early-write operation to be completed with OE \setminus grounded.

Data In/Out (DQ1 - DQ4)

The high-impedance output buffer provides direct TTL compatibility (no pullup resistor required) with a fanout of two Series 54 TTL loads. Data out is the same polarity as data in. The output is in the high-impedance (floating) state until CAS \setminus and OE \setminus are brought low. In a read cycle the output becomes valid after all access times are satisfied. The output remains valid while CAS \setminus and OE \setminus are low. CAS \setminus or OE \setminus going high returns it to the high-impedance state.

Output Enable (OE)

OE \setminus controls the impedance of the output buffers. When OE \setminus is high, the buffers remain in the high-impedance state. Bringing OE \setminus low during a normal cycle activates the output buffers, putting them in the low-impedance state. It is necessary for both RAS \setminus and CAS \setminus to be brought low for the output buffers to go into the low-impedance state. Once in the low-impedance state, they remain in the low-impedance state until either OE \setminus or CAS \setminus is brought high.

Refresh

A refresh operation must be performed at least once every 16ms to retain data. This can be achieved by strobing each of the 1024 rows (A0-A9). A normal read or write cycle refreshes all bits in each row that is selected. A RAS \setminus -only operation can be used by holding CAS \setminus at the high (inactive) level, conserving power as the output buffer remains in the high-impedance state. Externally generated addresses must be used for a RAS \setminus -only refresh. Hidden refresh can be performed while maintaining valid data at the output pin. This is accomplished by holding CAS \setminus at V_{IL} after a read operation and cycling RAS \setminus after a specified precharge period, similar to a RAS \setminus -only refresh cycle. The external address is ignored during the hidden refresh cycles.

CAS \setminus -before-RAS \setminus (CBR) and hidden refresh

CBR refresh is utilized by bringing CAS \setminus low earlier than RAS \setminus (see parameter t_{CSR}) and holding it low after RAS \setminus falls (see parameter t_{CSR}). For successive CBR refresh cycles, CAS \setminus can remain low while cycling RAS \setminus . The external address is ignored and the refresh address is generated internally. During CBR refresh cycles the outputs remain in the high-impedance state.

Hidden refresh can be performed while maintaining valid data at the output pins. This is accomplished by holding CAS \setminus at V_{IL} after a read operation. RAS \setminus is cycled after the specified read cycle parameters are met. Hidden refresh can also be used in conjunction with an early-write cycle. CAS \setminus is maintained at V_{IL} while RAS \setminus is cycled, once all the specified early-write parameters are met. Externally generated addresses must be used to specify the location to be accessed during the initial RAS \setminus cycle of a hidden refresh operation. Subsequent RAS \setminus cycles (refresh cycles) use the internally-generated addresses and the external address is ignored.

Power Up

To achieve proper device operation, an initial pause of 200 μ s followed by a minimum of eight initialization cycles is

(continued)



Power Up (continued)

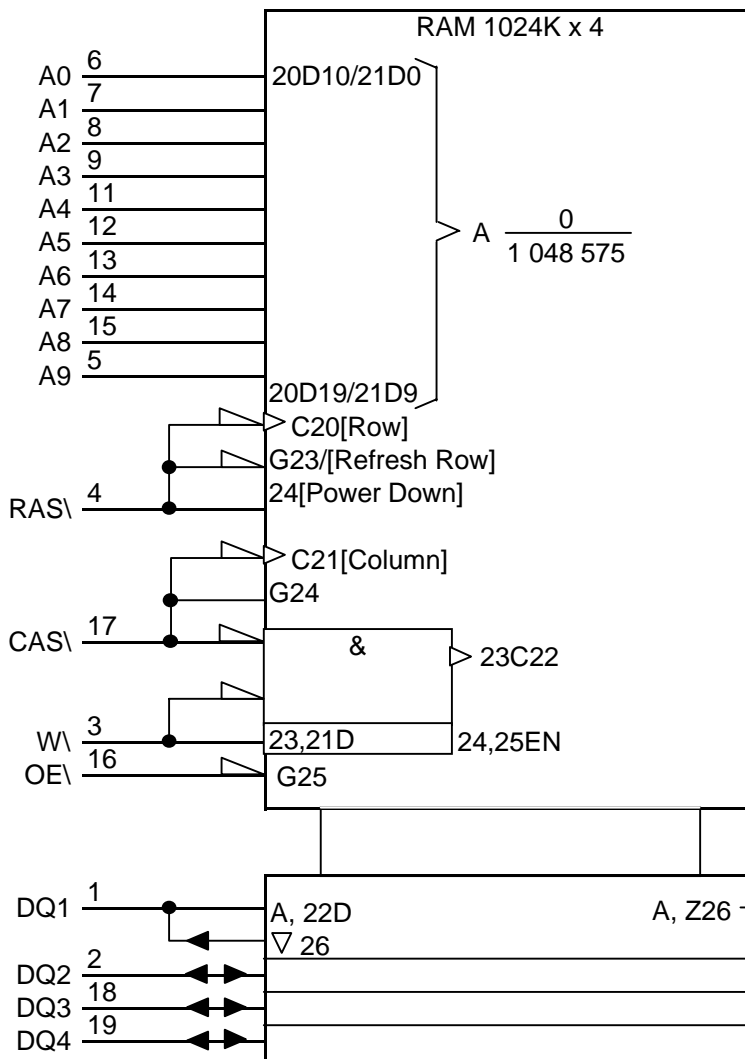
required after full Vcc level is achieved. These eight initialization cycles need to include at least one refresh (RAS\-only or CBR) cycle.

Test Mode

An industry standard Design For Test (DFT) mode is incorporated in the SMJ44400. A CBR with W\ low (WCBR) cycle is used to enter test mode. In the test mode, data is

written into and read from eight sections of the array in parallel. All data is written into the array through DQ1. Data is compared upon reading and if all bits are equal, all DQ pins go high. If any one bit is different, all the DQ pins go low. Any combination read, write, read-write, or page-mode can be used in the test mode. The test mode function reduces test times by enabling the 1M x 4-bit DRAM to be tested as if it were a 512K DRAM where column address 0 is not used. A RAS\-only or CBR refresh cycle is used to exit the DFT mode.

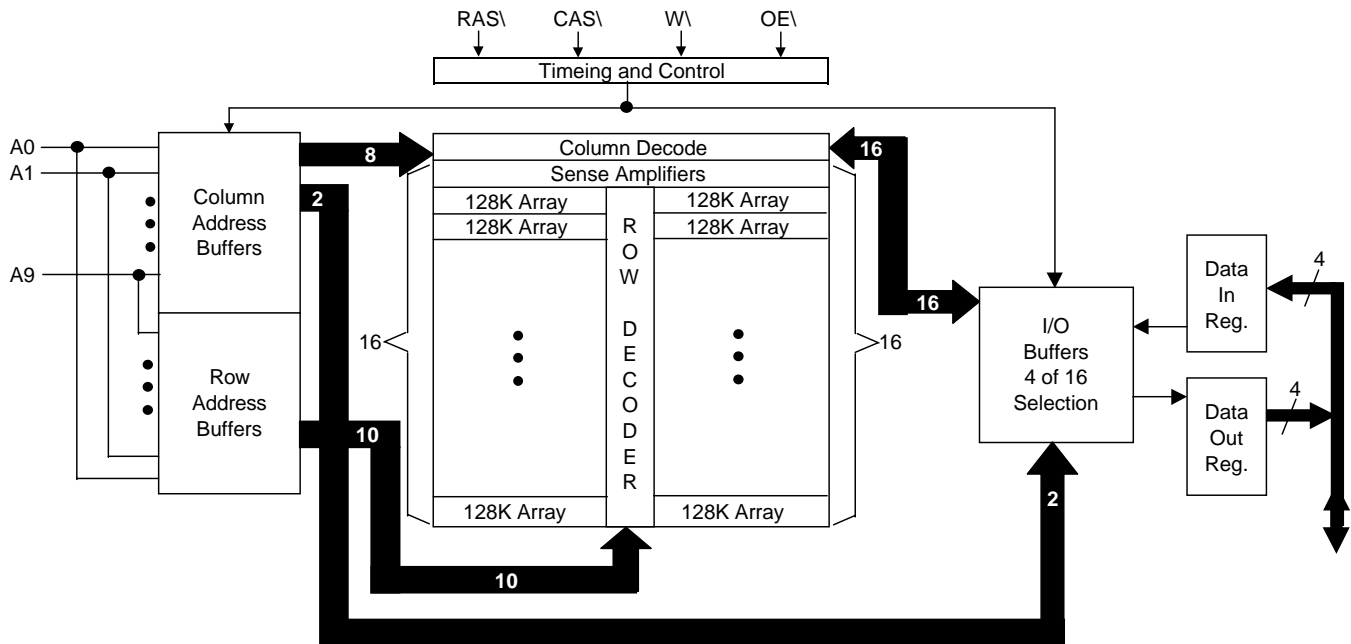
LOGIC SYMBOL¹



1. This symbol is in accordance with ANSI/IEEE Std. 91-1984 and IEC Publication 617-12. The pinouts illustrated are for the JD package.



FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS*

Voltage on V_{CC} Supply Relative to V_{SS}.....-1V to +7.0V
 Voltage Range on Any Pin Relative to V_{SS}.....-1V to +7.0V
 Short Circuit Output Current (per I/O).....50mA
 Power Dissipation.....1W
 Storage Temperature Range.....-65°C to +150°C
 Operating Temperature Range.....-55°C to +125°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

** Junction temperature depends upon package type, cycle time, loading, ambient temperature and airflow.

RECOMMENDED OPERATING CONDITIONS

SYM	DESCRIPTION	MIN	NOM	MAX	UNIT
V _{CC}	Supply Voltage	4.5	5	5.5	V
V _{IH}	High-Level Input Voltage	2.4		6.5	V
V _{IL}	Low-Level Input Voltage ¹	-1		0.8	V
T _A	Minimum Operating Temperature	-55			°C
T _C	Maximum Operating Case Temperature			125	°C

1. The algebraic convention, where the more negative (less positive) limit is designated as minimum, is used for logic-voltage levels only.



ELECTRICAL CHARACTERISTICS AND RECOMMENDED OPERATING CONDITIONS

($-55^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$ or -40°C to $+85^{\circ}\text{C}$; $V_{CC} = 5V \pm 10\%$)

SYM	PARAMETER	TEST CONDITIONS	-8		-10		-12		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
V _{OH}	High-level output voltage	I _{OH} = -5mA	2.4		2.4		2.4		V
V _{OL}	Low-level output voltage	I _{OL} = 4.2mA		0.4		0.4		0.4	V
I _I	Input current (leakage)	V _{CC} = 5.5V, V _I = 0V to 6.5V, All other pins = 0V to V _{CC}		±10		±10		±10	µA
I _O	Output current (leakage)	V _{CC} = 5.5V, V _O = 0V to V _{CC} , CAS\ High		±10		±10		±10	µA
I _{CC1}	Read - or write-cycle current ¹	V _{CC} = 5.5V, Minimum cycle		85		80		70	mA
I _{CC2}	Standby current	After 1 memory cycle, RAS\ and CAS\ High, V _{IH} = 2.4V		4		4		4	mA
I _{CC3}	Average refresh current (RAS\ only, or CBR\) ¹	V _{CC} = 5.5V, Minimum cycle, RAS\ cycling, CAS\ High (RAS\ only), RAS\ Low after CAS\ Low (CBR)		85		75		65	mA
I _{CC4}	Average page current ²	V _{CC} = 5.5V, t _{PC} = minimum, RAS\ Low, CAS\ cycling		50		40		35	mA

CAPACITANCE (f = 1MHz)³

SYM	PARAMETER	MAX	UNIT
C _{i(A)}	Input capacitance, address inputs	7	pF
C _{i(RC)}	Input capacitance, strobe inputs	10	pF
C _{i(W)}	Input capacitance, write-enable inputs	10	pF
C _O	Output capacitance	10	pF

SWITCHING CHARACTERISTICS ($-55^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$ or -40°C to $+85^{\circ}\text{C}$; $V_{CC} = 5V \pm 10\%$)

SYM	PARAMETERS	-8	-10	-12	UNIT
		MAX	MAX	MAX	
t _{AA}	Access time from column address	40	45	55	ns
t _{CAC}	Access time from CAS\ low	20	25	30	ns
t _{CPA}	Access time from column precharge	45	50	55	ns
t _{RAC}	Access time from RAS\ low	80	100	120	ns
t _{OEa}	Access time from OE\ low	20	25	30	ns
t _{OFF}	Output disable time after CAS\ High ⁴	20	25	30	ns
t _{OEZ}	Output disable time after OE\ High ⁴	20	25	30	ns

NOTES:

1. Measured with a maximum of one address change while RAS\ = V_{IL}.
2. Measured with a maximum of one address change while CAS\ = V_{IH}.
3. V_{CC} = 5V ±0.5V and the bias on the pins under test is 0V. Capacitance is sampled only at initial design and after any major change.
4. t_{OFF} and t_{OEZ} are specified when the output is no longer driven. The outputs are disabled by bringing either OE\ or CAS\ High.



TIMING REQUIREMENTS ($-55^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$ or -40°C to $+85^{\circ}\text{C}$; $V_{CC} = 5\text{V} \pm 10\%$)

SYM	PARAMETER	-8		-10		-12		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{RC}	Cycle time, random read or write ¹	150		180		210		ns
t _{RWC}	Cycle time, read-write	205		245		285		ns
t _{PC}	Cycle time, page-mode read or write ²	50		60		65		ns
t _{PRWC}	Cycle time, page-mode read-write	100		120		135		ns
t _{RASP}	Pulse duration, page mode, RAS\ low ³	80	100000	100	100000	120	100000	ns
t _{RAS}	Pulse duration, nonpage mode, RAS\ low ³	80	10000	100	10000	120	10000	ns
t _{CAS}	Pulse duration, CAS\ low ⁴	20	10000	25	10000	30	10000	ns
t _{CP}	Pulse duration, CAS\ High	10		10		15		ns
t _{RP}	Pulse duration, RAS\ High (precharge)	60		70		80		ns
t _{WP}	Pulse duration, write	15		20		25		ns
t _{ASC}	Setup time, column address before CAS\ low	0		0		0		ns
t _{ASR}	Setup time, row address before RAS\ low	0		0		0		ns
t _{DS}	Setup time, data ⁵	0		0		0		ns
t _{RCS}	Setup time, read before CAS\ low	0		0		0		ns
t _{CWL}	Setup time, W\ low before CAS\ high	20		25		30		ns
t _{RWL}	Setup time, W\ low before RAS\ high	20		25		30		ns
t _{WCS}	Setup time, W\ low before CAS\ low (early-write operation only)	0		0		0		ns
t _{WSR}	Setup time, W\ High (CBR refresh only)	10		10		10		ns
t _{CAH}	Hold time, column address after CAS\ low	15		20		20		ns
t _{DHR}	Hold time, data after RAS\ low	60		75		90		ns
t _{DH}	Hold time, data ⁵	15		20		25		ns
t _{AR}	Hold time, column address after CAS\ low ⁴	60		75		90		ns
t _{RAH}	Hold time, row address after RAS\ low	10		15		15		ns
t _{RCH}	Hold time, read after CAS\ High ⁶	0		0		0		ns
t _{RRH}	Hold time, read after RAS\ High ⁶	0		0		0		ns
t _{WCH}	Hold time, write after CAS\ low (early-write operation only)	15		20		25		ns
t _{WCR}	Hold time, write after RAS\ low ⁴	60		75		90		ns
t _{WHR}	Hold time, W\ High (CBR refresh only)	10		10		10		ns
t _{OEH}	Hold time, OE\ command	20		25		30		ns
t _{ROH}	Hold time, RAS\ referenced to OE\	20		25		30		ns
t _{AWD}	Delay time, column address to W\ low (read-write operation only)	70		80		90		ns
t _{CHR}	Delay time, RAS\ low to CAS\ High (CBR refresh only)	20		20		25		ns
t _{CRP}	Delay time, CAS\ High to RAS\ low	0		0		0		ns
t _{CSH}	Delay time, RAS\ low to CAS\ High	80		100		120		ns
t _{CSR}	Delay time, CAS\ low to RAS\ low (CBR refresh only)	10		10		10		ns
t _{CWD}	Delay time, CAS\ low to W\ low (read-write operation only)	50		60		70		ns

NOTES:

1. All cycle times assume $t_T = 5\text{ns}$.
2. To assure t_{PC} min, t_{ASC} should be $\geq t_{CP}$.
3. In a read-write cycle, t_{RWD} and t_{RWL} must be observed.
4. In a read-write cycle, t_{CWD} and t_{CWL} must be observed.
5. Referenced to the later of CAS\ or W\ in write operations.
6. Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.



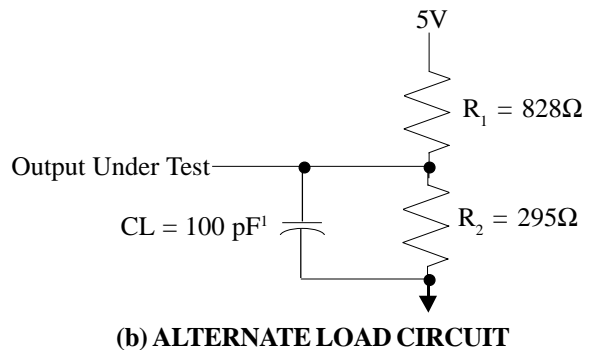
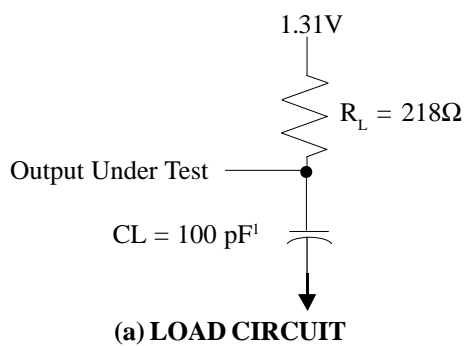
TIMING REQUIREMENTS (continued)

SYM	PARAMETER	-8		-10		-12		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{RAD}	Delay time, RAS\ low to column address ¹	15	40	20	50	20	65	ns
t _{RAL}	Delay time, column addresss to RAS\ High	40		50		55		ns
t _{CAL}	Delay time, column addresss to CAS\ High	40		50		55		ns
t _{RCD}	Delay time, RAS\ low to CAS\ low ¹	20	60	25	75	25	90	ns
t _{RPC}	Delay time, RAS\ High to CAS\ low	0		0		0		ns
t _{RSH}	Delay time, CAS\ low to RAS\ High	20		25		30		ns
t _{RWD}	Delay time, RAS\ low to W\ low (read-write operation only)	110		135		160		ns
t _{CLZ}	CAS\ to output in low Z ²	0		0		0		ns
t _{OED}	OE\ to data delay	20		25		30		ns
t _{REF}	Refresh time interval		16		16		16	ms
t _T	Tranistion time ³							

NOTES:

1. Maximum value specified only to assure access time.
2. Valid data is presented at the outputs after all access times are satisfied but can go from the high-impedance state to an invalid-data state prior to the specified access times as the outputs are driven when CAS\ and OE\ are low.
3. Transition times (rise and fall) for RAS\ and CAS\ are to be a minimum of 3ns and a maximum of 50ns.

PARAMETER MEASUREMENT INFORMATION
Figure 1. Load Circuit for Timing Parameters

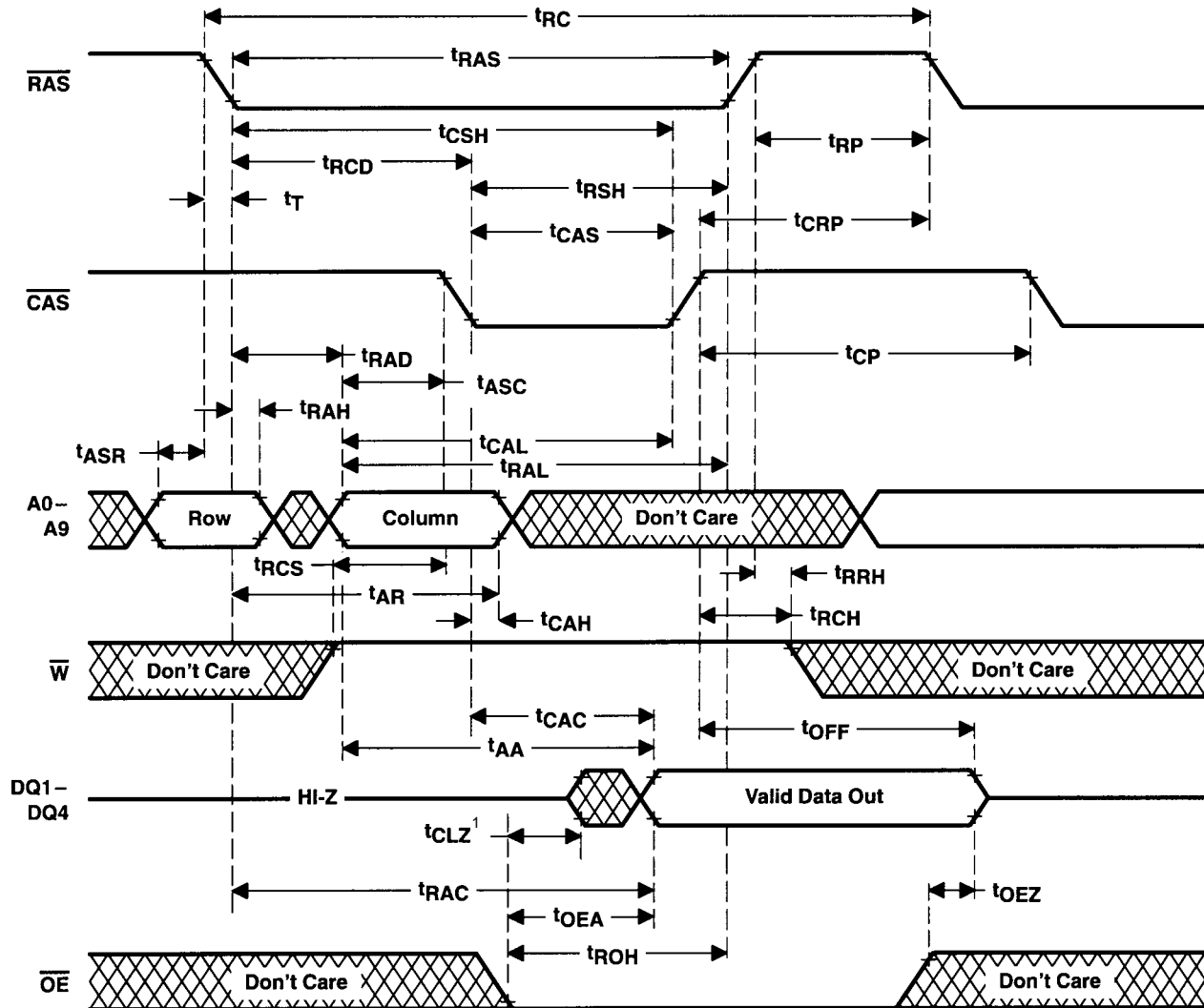


NOTES:

1. C_L includes probe and fixture capacitance.



READ-CYCLE TIMING

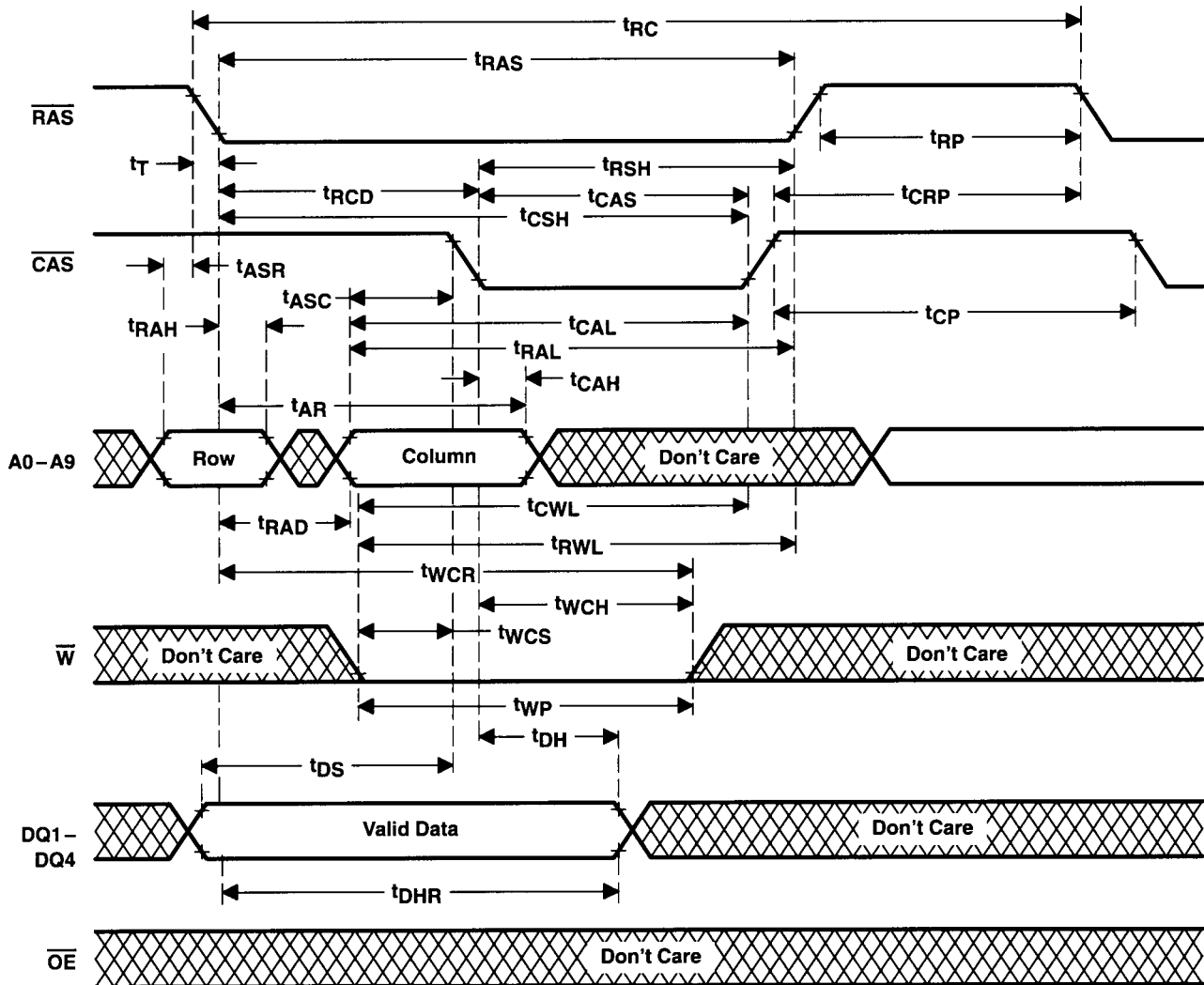


NOTES:

1. Valid data is presented at the outputs after all access times are satisfied but can go from the high-impedance state to an invalid-data state prior to the specified access times as the outputs are driven when CAS $\bar{}$ and OE are low.

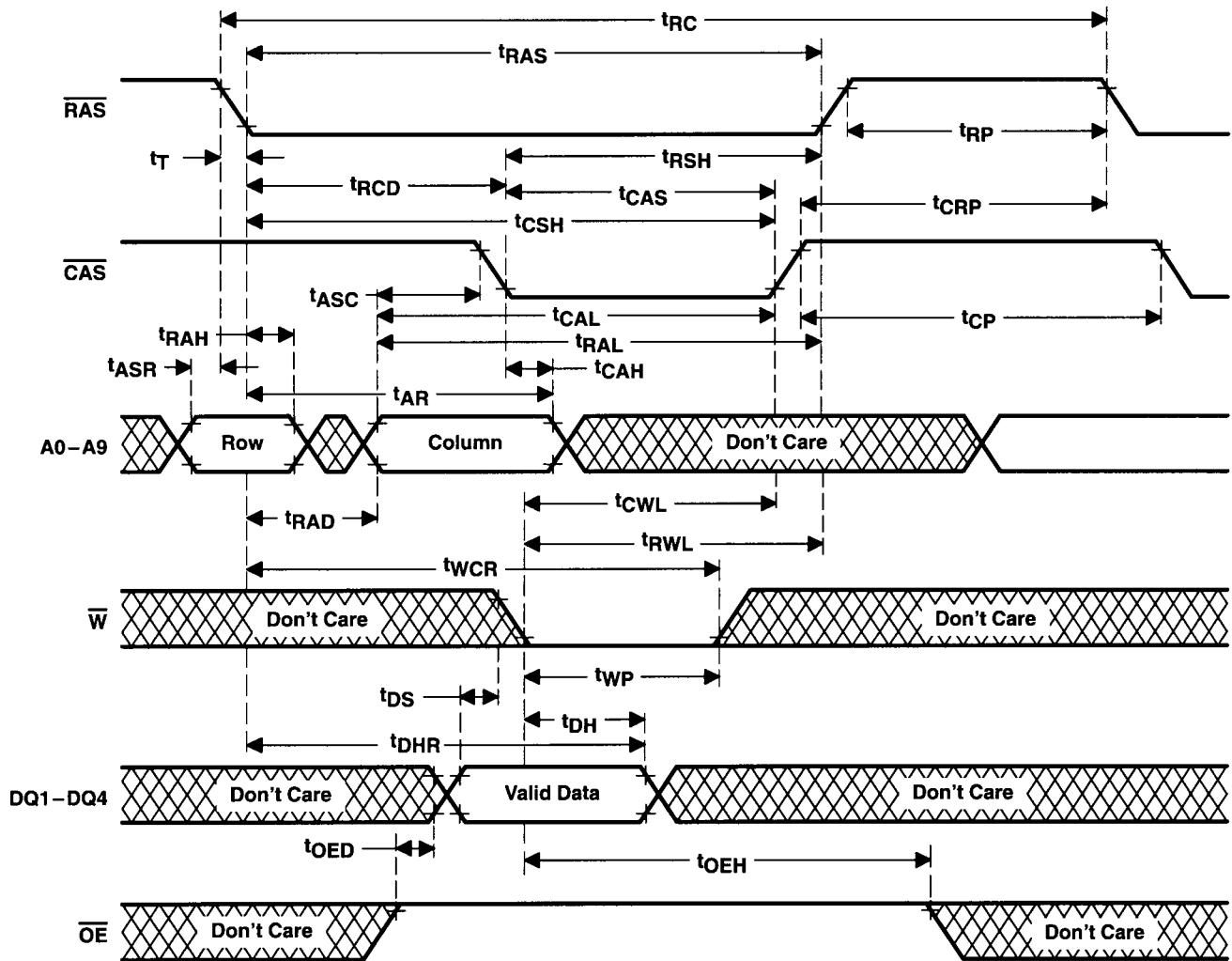


EARLY-WRITE-CYCLE TIMING



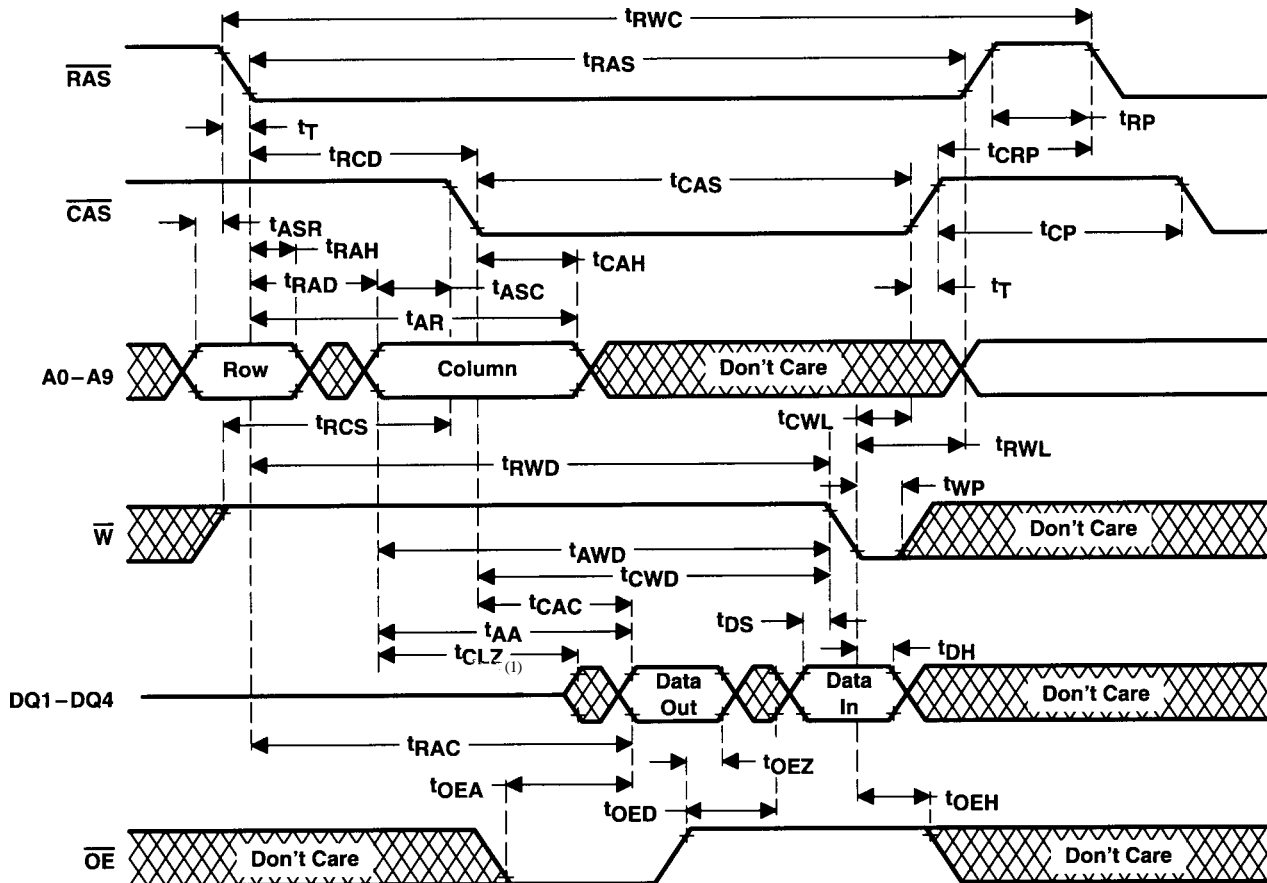


WRITE-CYCLE TIMING





READ-WRITE CYCLE TIMING

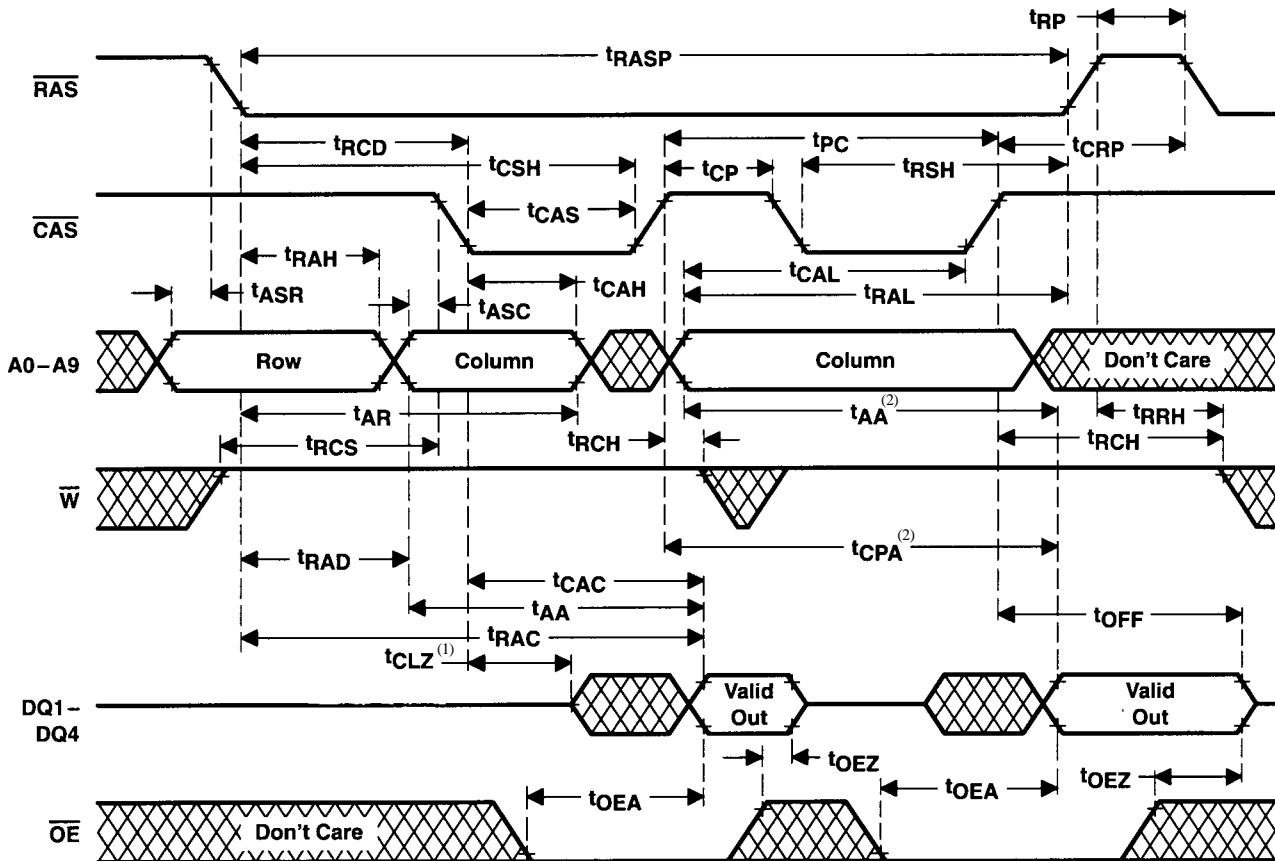


NOTES:

1. Valid data is presented at the outputs after all access times are satisfied but can go from the high-impedance state to an invalid-data state prior to the specified access times as the outputs are driven when CAS and OE are low.



ENHANCED-PAGE-MODE READ-CYCLE TIMING



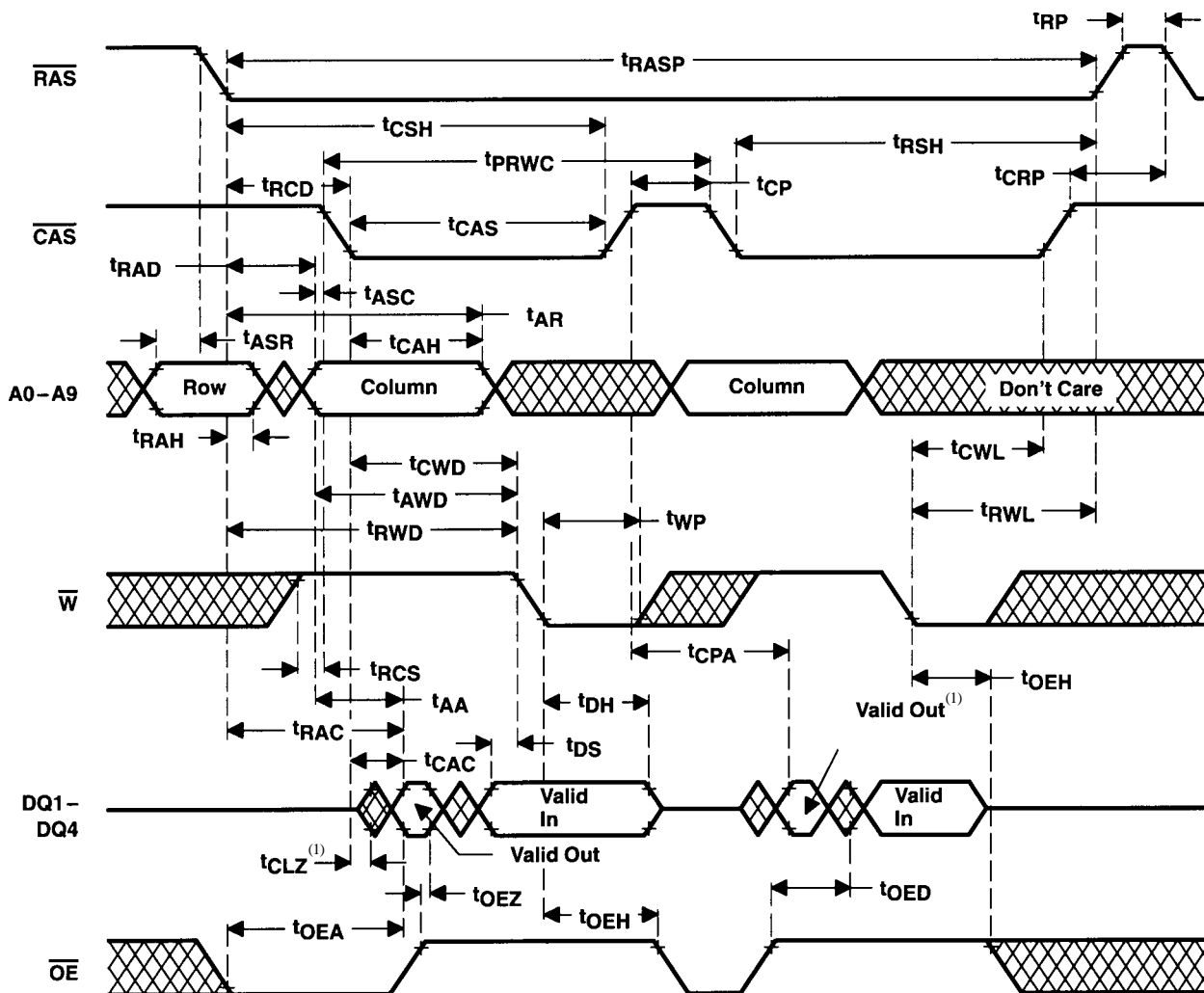
NOTES:

1. Valid data is presented at the outputs after all access times are satisfied but can go from the high-impedance state to an invalid-data state prior to the specified access times as the outputs are driven when CAS\ and OE\ are low.

2. Access time is $t_{CPA}^{(2)}$ or t_{AA} dependent.



ENHANCED-PAGE-MODE READ-WRITE-CYCLE TIMING²

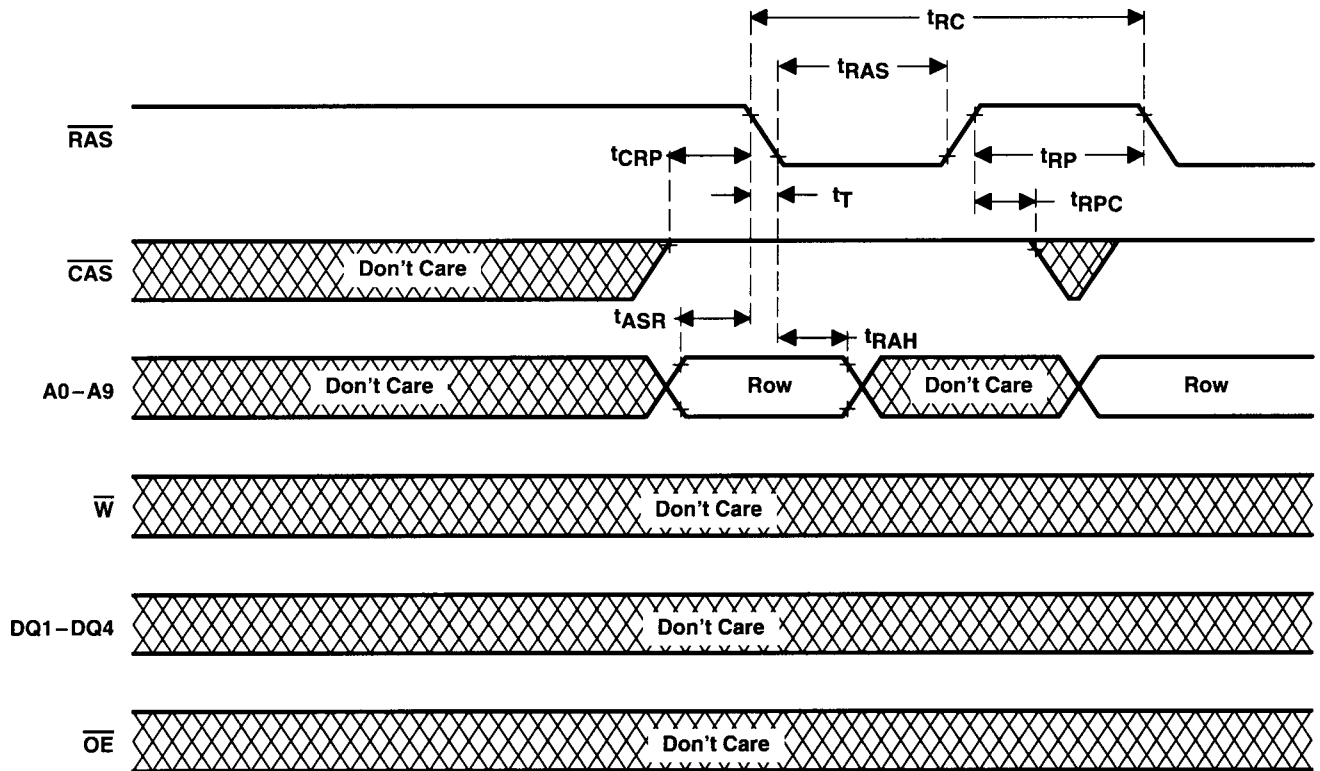


NOTES:

- Valid data is presented at the outputs after all access times are satisfied but can go from the high-impedance state to an invalid-data state prior to the specified access times as the outputs are driven when CAS and OE are low.
- A read or write cycle can be intermixed with read-write cycles as long as the read and write timing specifications are not violated.

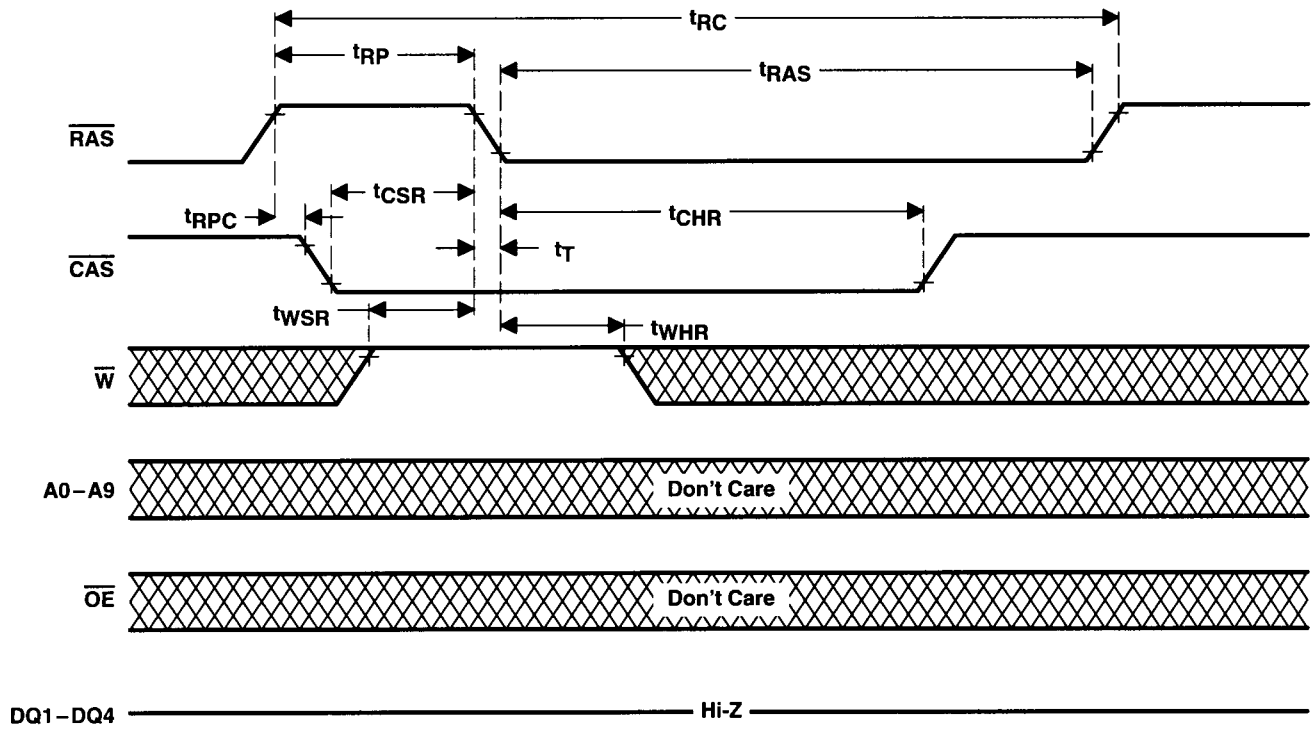


RAS-ONLY REFRESH TIMING



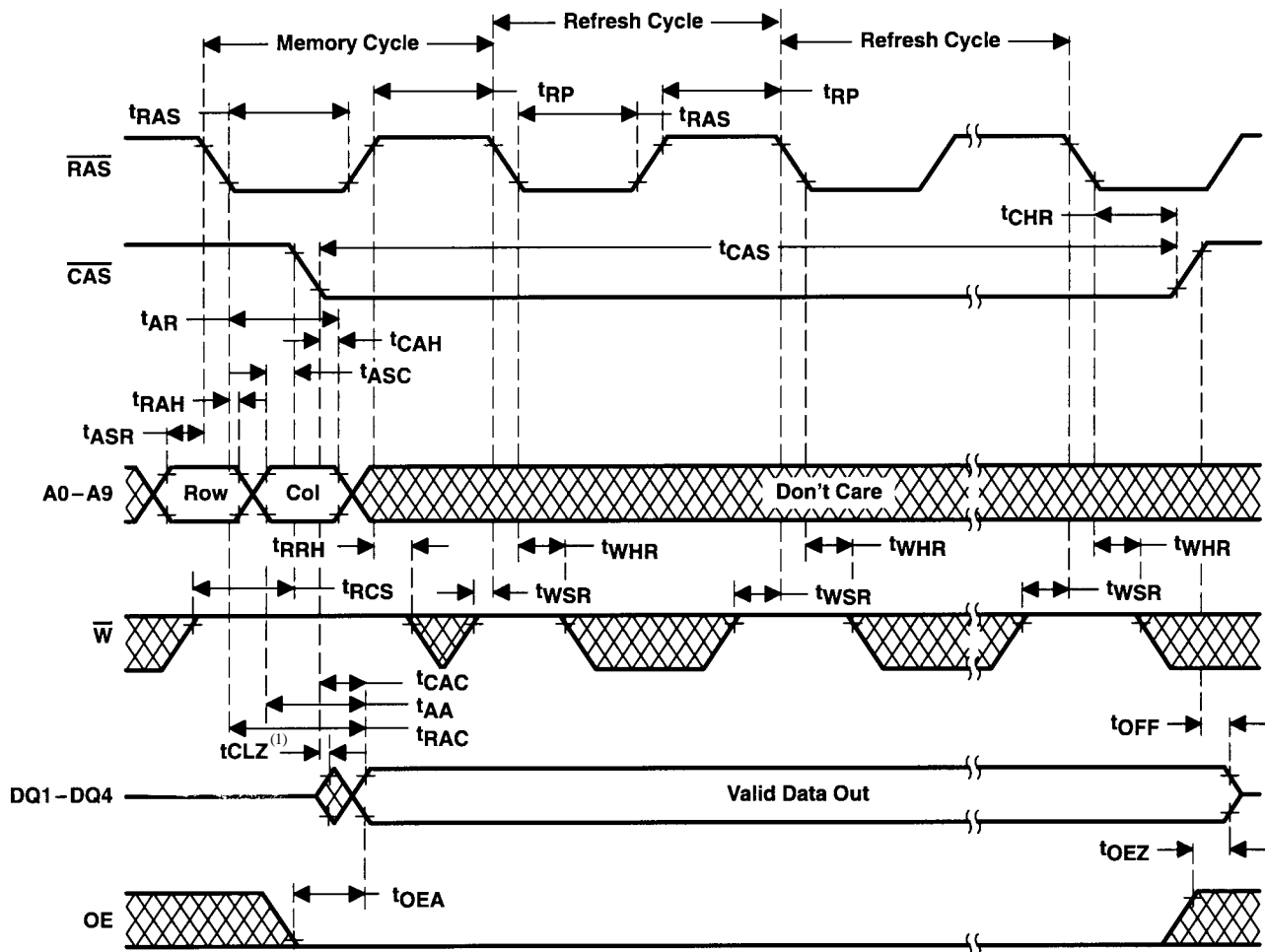


AUTOMATIC-CBR-REFRESH-CYCLE TIMING





HIDDEN-REFRESH-CYCLE (READ) TIMING



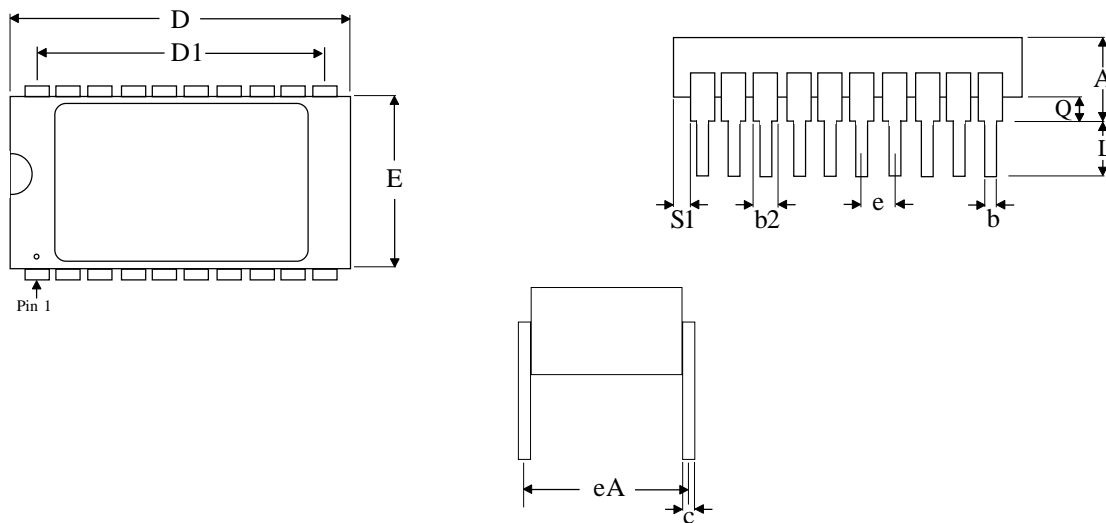
NOTES:

1. Valid data is presented at the outputs after all access times are satisfied but can go from the high-impedance state to an invalid-data state prior to the specified access times as the outputs are driven when CAS and OE are low.



MECHANICAL DEFINITIONS*

ASI Case #113 (Package Designator JD)
SMD 5962-90847, Case Outline U



SYMBOL	SMD Specifications	
	MIN	MAX
A	---	0.175
b	0.015	0.021
b2	0.045	0.065
c	0.008	0.014
D	0.980	1.030
D1	0.890	0.910
E	0.380	0.410
eA	0.385	0.420
e	0.100 BSC	
Q	0.015	0.060
L	0.125	0.200
S1	---	0.070

NOTE: These dimensions are per the SMD. ASI's package dimensional limits may differ, but they will be within the SMD limits.

* All measurements are in inches.



ORDERING INFORMATION

EXAMPLE: SMJ44400JD-12/XT

Device Number	Package Type	Speed ns	Process
SMJ44400	JD	-8	/*
SMJ44400	JD	-10	/*
SMJ44400	JD	-12	/*

*AVAILABLE PROCESSES

IT = Industrial Temperature Range

-40°C to +85°C

XT = Extended Temperature Range

-55°C to +125°C

883C = Full Military Processing

-55°C to +125°C



Austin Semiconductor, Inc.

DRAM
SMJ44400

ASI TO DSCC PART NUMBER CROSS REFERENCE*

ASI Package Designator JD

<u>TI Part #**</u>	<u>SMD Part #</u>
SMJ44400-12/JDM	5962-9084701MUA
SMJ44400-10/JDM	5962-9084702MUA
SMJ44400-80/JDM	5962-9084703MUA

* ASI part number is for reference only. Orders received referencing the SMD part number will be processed per the SMD.

** Parts are listed on SMD under the old Texas Instruments part number. ASI purchased this product line in November of 1999.